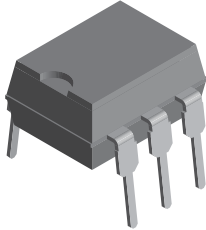
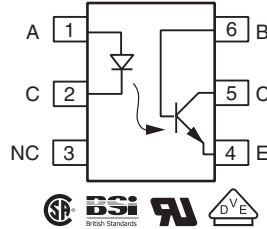


## Optocoupler, Phototransistor Output, with Base Connection, 300 V $BV_{CE0}$



H179004-3



### FEATURES

- Good CTR linearity with forward current
- Low CTR degradation
- Very high collector emitter breakdown voltage,  $BV_{CE0} = 300\text{ V}$
- Isolation test voltage:  $5300\text{ V}_{RMS}$
- Low coupling capacitance
- High common mode transient immunity
- Phototransistor optocoupler 6 pin DIP package with base connection
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC


**RoHS**  
COMPLIANT

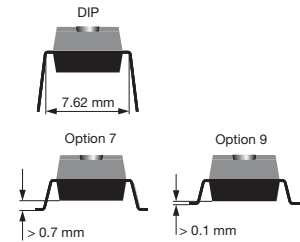
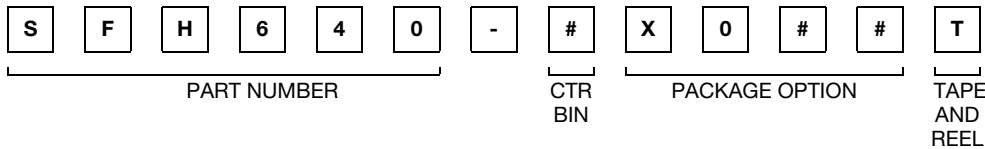
### DESCRIPTION

The SFH640 is an optocoupler with very high  $BV_{CE0}$ , a minimum of 300 V. It is intended for telecommunications applications or any DC application requiring a high blocking voltage.

### AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-2 (VDE 0884) available with option 1
- CSA 93751
- BSI IEC 60950; IEC 60065

### ORDERING INFORMATION



AGENCY CERTIFIED/PACKAGE	CTR (%)	
	10 mA	
<b>UL, CSA, BSI</b>	<b>63 to 125</b>	<b>100 to 200</b>
DIP-6	SFH640-2	SFH640-3
SMD-6, option 7	SFH640-2X007	SFH640-3X007T <sup>(1)</sup>
<b>VDE, UL, CSA, BSI</b>	<b>63 to 125</b>	<b>100 to 200</b>
SMD-6, option 9	-	SFH640-3X019T <sup>(1)</sup>

#### Notes

- Additional options may be possible, please contact sales office.
- <sup>(1)</sup> Also available in tubes, do not put T on the end.

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT</b>				
Reverse voltage		$V_R$	6.0	V
DC forward current		$I_F$	60	mA
Surge forward current	$t_p \leq 10\text{ }\mu\text{s}$	$I_{FSM}$	2.5	A
Total power dissipation		$P_{diss}$	100	mW



ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>OUTPUT</b>				
Collector emitter voltage		$V_{CEO}$	300	V
Collector base voltage		$V_{CBO}$	300	V
Emitter base voltage		$V_{EBO}$	7.0	V
Collector current		$I_C$	50	mA
Surge collector current	$t_p \leq 10\text{ ms}$	$I_C$	100	mA
Total power dissipation		$P_{diss}$	300	mW
<b>COUPLER</b>				
Isolation test voltage between emitter and detector		$V_{ISO}$	5300	$V_{RMS}$
			7500	$V_{PK}$
Isolation resistance	$V_{IO} = 500\text{ V}, T_{amb} = 25\text{ }^{\circ}\text{C}$	$R_{IO}$	$\geq 10^{12}$	$\Omega$
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ }^{\circ}\text{C}$	$R_{IO}$	$\geq 10^{11}$	$\Omega$
Insulation thickness between emitter and detector			$\geq 0.4$	mm
Creepage distance			$\geq 7$	mm
Clearance distance			$\geq 7$	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1		CTI	175	
Storage temperature range		$T_{stg}$	- 55 to + 150	$^{\circ}\text{C}$
Operating temperature range		$T_{amb}$	- 55 to + 100	$^{\circ}\text{C}$
Soldering temperature <sup>(1)</sup>	max. 10 s, dip soldering: distance to seating plane $\geq 1.5\text{ mm}$	$T_{sld}$	260	$^{\circ}\text{C}$

**Notes**

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- <sup>(1)</sup> Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

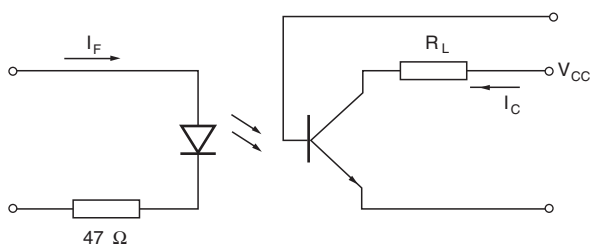
ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>							
Forward voltage	$I_F = 10\text{ mA}$		$V_V$		1.1	1.5	V
Reverse voltage	$I_R = 10\text{ }\mu\text{A}$		$V_R$	6			V
Reverse current	$V_R = 6\text{ V}$		$I_R$		0.01	10	$\mu\text{A}$
Capacitance	$V_F = 0\text{ V}, f = 1\text{ MHz}$		$C_O$		25		pF
Thermal resistance			$R_{thja}$		750		K/W
<b>OUTPUT</b>							
Collector emitter breakdown voltage	$I_{CE} = 1\text{ mA}, R_{BE} = 1\text{ M}\Omega$		$BV_{CER}$	300			V
Voltage emitter base	$I_{EB} = 10\text{ }\mu\text{A}$		$BV_{BEO}$	7			V
Collector emitter capacitance	$V_{CE} = 10\text{ V}, f = 1\text{ MHz}$		$C_{CE}$		7		pF
Collector base capacitance	$V_{CB} = 10\text{ V}, f = 1\text{ MHz}$		$C_{CB}$		8		pF
Emitter base capacitance	$V_{EB} = 5\text{ V}, f = 1\text{ MHz}$		$C_{EB}$		38		pF
Thermal resistance			$R_{thja}$		250		K/W
<b>COUPLER</b>							
Coupling capacitance			$C_C$		0.6		pF
Saturation voltage collector emitter	$I_F = 10\text{ mA}, I_C = 3.2\text{ mA}$	SFH640-2	$V_{CEsat}$		0.25	0.4	V
	$I_F = 10\text{ mA}, I_C = 5\text{ mA}$	SFH640-3	$V_{CEsat}$		0.25	0.4	V
Collector emitter leakage current	$V_{CE} = 200\text{ V}, R_{BE} = 1\text{ M}\Omega$		$I_{CER}$		1	100	nA

**Note**

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

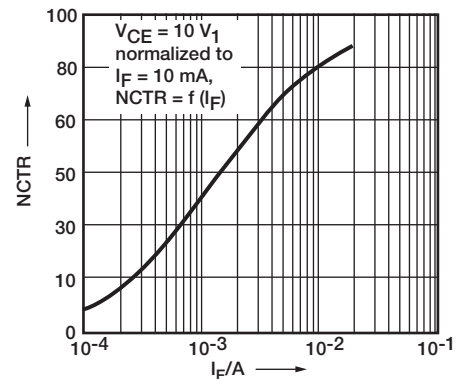
<b>CURRENT TRANSFER RATIO</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$I_F = 10\text{ mA}$ , $V_{CE} = 10\text{ V}$	SFH640-2	$I_C/I_F$	63		125	%
	$I_F = 1\text{ mA}$ , $V_{CE} = 10\text{ V}$	SFH640-2	$I_C/I_F$	22	45		%
	$I_F = 10\text{ mA}$ , $V_{CE} = 10\text{ V}$	SFH640-3	$I_C/I_F$	100		200	%
	$I_F = 1\text{ mA}$ , $V_{CE} = 10\text{ V}$	SFH640-3	$I_C/I_F$	34	70		%

<b>SWITCHING CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Turn-on time	$I_C = 2\text{ mA}$ , $R_L = 100\text{ }\Omega$ , $V_{CC} = 10\text{ V}$	$t_{on}$		5		$\mu\text{s}$	
Rise time	$I_C = 2\text{ mA}$ , $R_L = 100\text{ }\Omega$ , $V_{CC} = 10\text{ V}$	$t_r$		2.5		$\mu\text{s}$	
Turn-off time	$I_C = 2\text{ mA}$ , $R_L = 100\text{ }\Omega$ , $V_{CC} = 10\text{ V}$	$t_{off}$		6		$\mu\text{s}$	
Fall time	$I_C = 2\text{ mA}$ , $R_L = 100\text{ }\Omega$ , $V_{CC} = 10\text{ V}$	$t_f$		5.5		$\mu\text{s}$	

**TYPICAL CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)


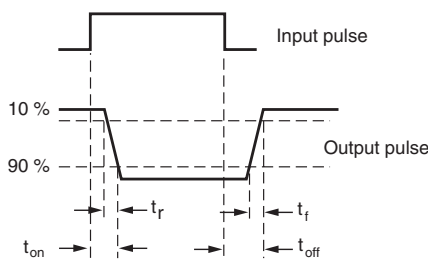
isfh640\_01a

Fig. 1 - Switching Times Measurement Test Circuit and Waveform



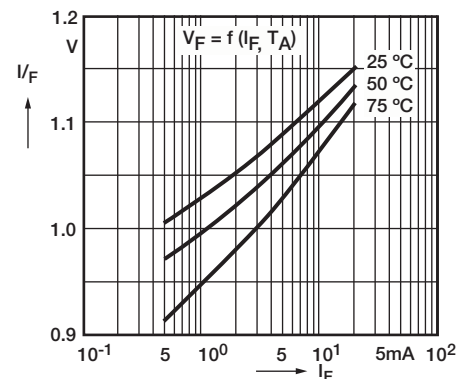
isfh640\_02

Fig. 3 - Current Transfer Ratio (typ.)



isfh640\_01b

Fig. 2 - Switching Times Measurement Test Circuit and Waveform



isfh640\_03

Fig. 4 - Diode Forward Voltage (typ.)

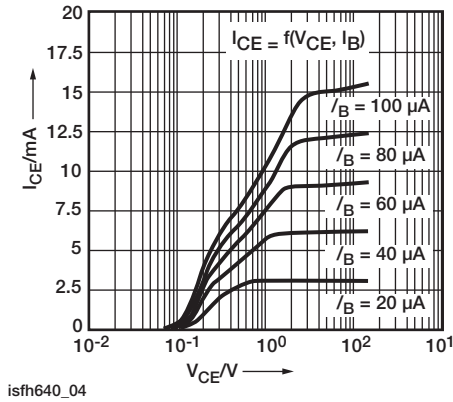


Fig. 5 - Output Characteristics (typ.)

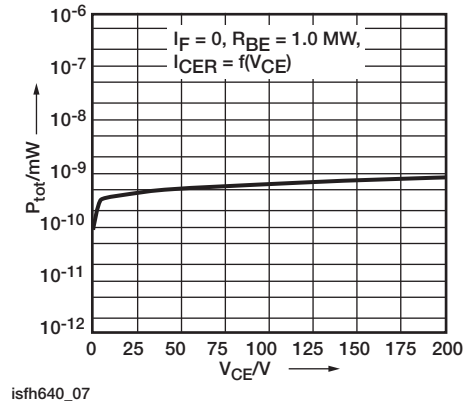


Fig. 8 - Collector-Emitter Leakage Current (typ.)

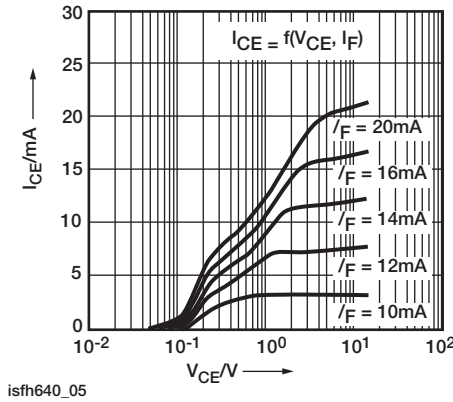


Fig. 6 - Output Characteristics (typ.)

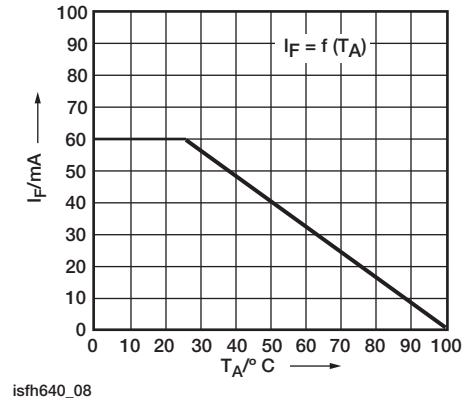


Fig. 9 - Permissible Loss Diode

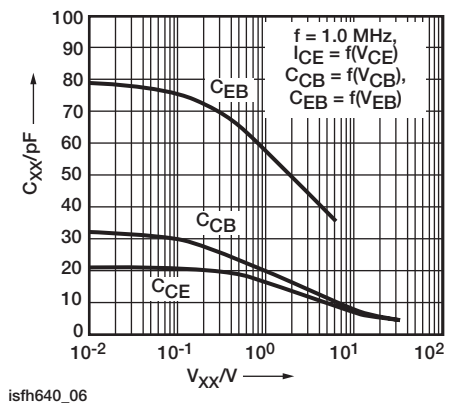


Fig. 7 - Transistor Capacitances (typ.)

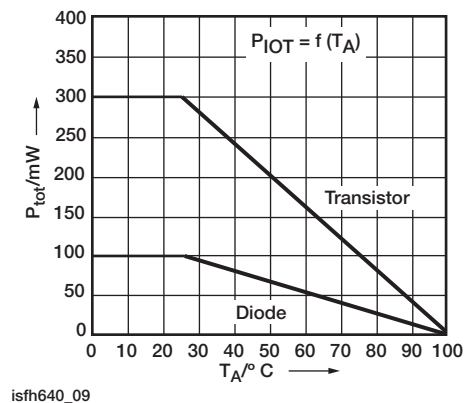
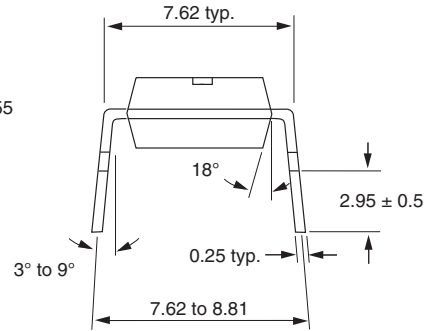
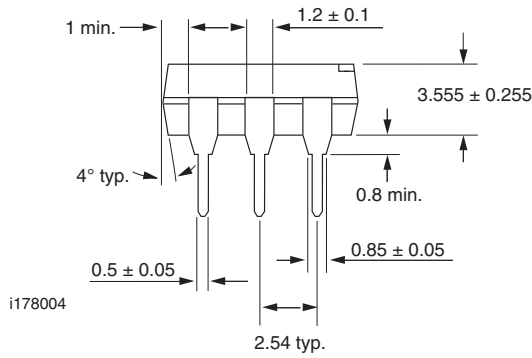
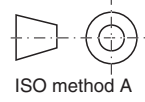
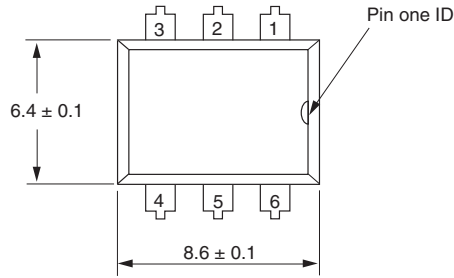
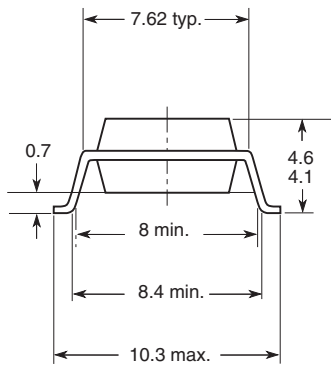


Fig. 10 - Permissible Power Dissipation

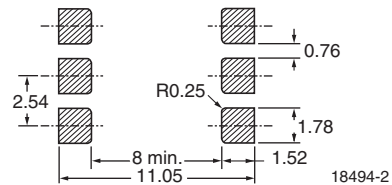
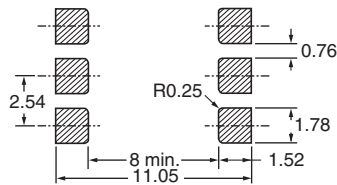
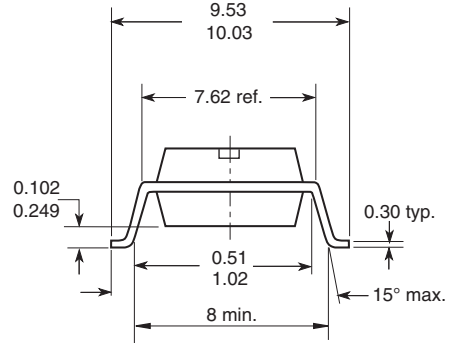
**PACKAGE DIMENSIONS** in millimeters



**Option 7**



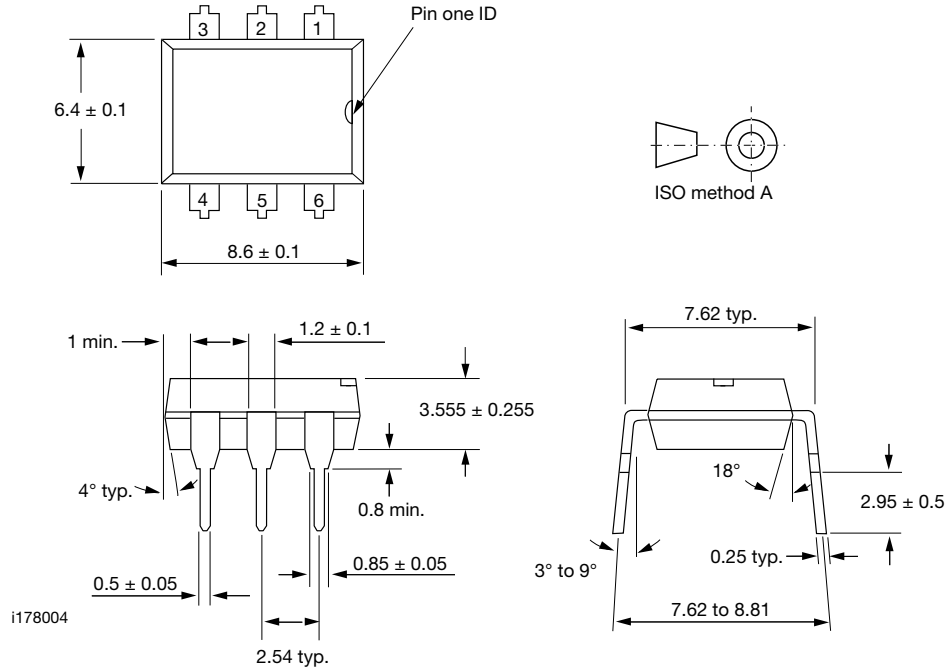
**Option 9**





# DIP-6A

## PACKAGE DIMENSIONS in inches (millimeters)



### Note

The information in this document provides generic information but for specific information on a product the appropriate product datasheet should be used.



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